

DEFORMATION IMPURITY REDISTRIBUTION  
IN THE HETEROSYSTEMS WITH STRESSED  
LAYERS

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S u m m a r y

In the frames of a diffusion model modified by mechanical and deformation effects, a method of impurity stationary profile is proposed. The presence of stressed layers in heterosystems is shown to result in the redistribution of impurities. In particular, impurities are stored in the stressed layers of a heterostructure, which consequently leads to a decrease in the concentration of impurities in the non-deformed part of a crystal. In stressed layers with tension deformation, the impurity concentration is reduced, but it increases in the non-deformed part of a heterostructure.